



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
-30V	19mΩ @ Vgs = -10V	-8.7A
-307	$45m\Omega$ @ Vgs = -4.5V	-5.5A

Features and Benefits

- 0.6mm profile ideal for low profile applications
- Low Gate Threshold Voltage
- Low On-Resistance
- ESD protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

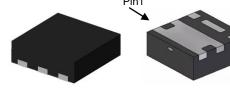
- Battery Management Application
- Power Management Functions
- DC-DC Converters

Mechanical Data

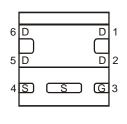
- Case: U-DFN2020-6 (Type E)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.007 grams (Approximate)



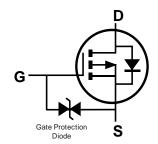








Pin Out Bottom View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3026SFDE-7	U-DFN2020-6 (Type E)	3,000/Tape & Reel
DMP3026SFDE-13	U-DFN2020-6 (Type E)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



7P = Product Type Marking Code YM = Date Code Marking Y = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	2016		2017	2018		2019	2020		2021	2022		2023
Code	D		Е	F		G	Н			J		K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V _{DSS}	-30	V		
Gate-Source Voltage	V _{GSS}	±25	V		
Continuous Dusin Compart (Nata C) V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-8.7 -6.9	А
Continuous Drain Current (Note 6) V _{GS} = -10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-10.4 -8.4	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	-50	A		
Continuous Source-Drain Diode Current (Note 6)	Is	-2.0	А		
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	-23	А		
Avalanche Energy (Note 7) L = 0.1mH	Eas	27	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Total Dawer Discipation (Note 5)	T _A = +25°C	_	0.72	W	
Total Power Dissipation (Note 5)	$T_A = +70^{\circ}C$	P_{D}	0.46		
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	0	175	°C/W	
memiai Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	121		
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	٥	2.0	W	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	P_{D}	1.3		
Thermal Peciatones Junction to Ambient (Note 6)	Steady state	0	61	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{ hetaJA}$	42		
Thermal Resistance, Junction to Case (Note 6)	Steady state	$R_{ heta JC}$	9.3		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$VGS = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C			_	-1		Vps = -24V, VGS = 0V	
Zero Gate Voltage Drain Current TJ = +150°C (Note 9)	I _{DSS}	1	_	-100	μA	VDS = -24V, VGS = 0V	
Gate-Source Leakage	I _{GSS}		_	±10	μΑ	$Vgs = \pm 25V$, $VDS = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(th)}$	-1	_	-3	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			15	19		VGS = -10V, ID = -4.5A	
Static Drain-Source On-Resistance	R _{DS (ON)}	_	28	45	mΩ	Vgs = -4.5V, ID = -3.5A	
			34	54		VGS = -4.0V, $ID = -3.0A$	
Diode Forward Voltage	V _{SD}	l	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1.0A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	-	1,204	_		15) / 15) / 1	
Output Capacitance	Coss	1	154	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	I	112			1 = 1:001112	
Gate Resistance	R_g		16	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -10V)	Q_g		19.6	_			
Total Gate Charge (V _{GS} = -4.5V)	Q_g	I	9.2		nC	$V_{DS} = -15V, I_{D} = -9.5A$	
Gate-Source Charge	Q_{gs}		4.3	_	110	VDS = -15V, ID = -9.5A	
Gate-Drain Charge	Q_{gd}	_	3.9	_			
Turn-On Delay Time	t _{D(on)}	_	5.3	_			
Turn-On Rise Time	t _r	_	23	_	20	$V_{DS} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time	t _{D(off)}	_	34	_	ns	$R_G = 6\Omega$, $I_D = -9.5A$	
Turn-Off Fall Time	t _f		26	_			
Reverse Recovery Time	t _{rr}		10	_	ns	1 0.54 11/14 4004/	
Reverse Recovery Charge	Q _{rr}		3.3	_	nC	$I_F = -9.5A$, di/dt = 100A/ μ s	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

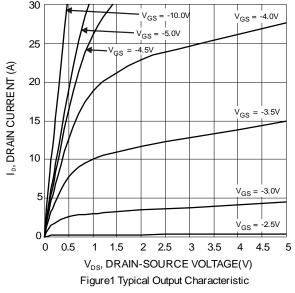
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

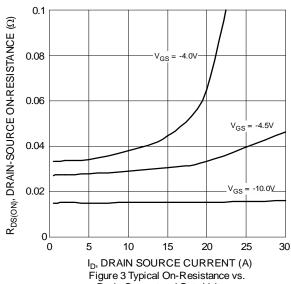
7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep $T_J=25^{\circ}C.$

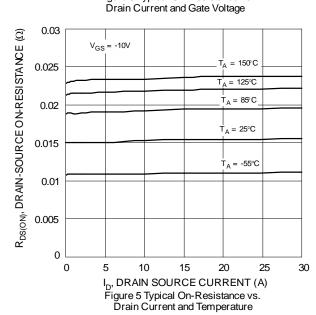
8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.









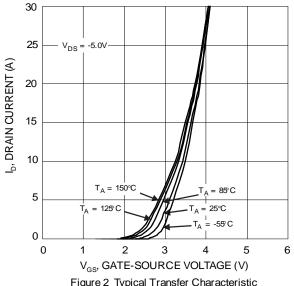
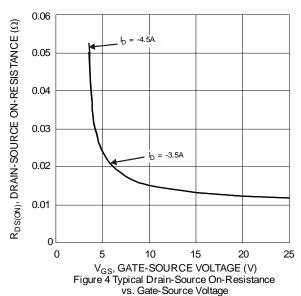


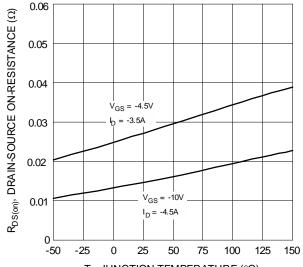
Figure 2 Typical Transfer Characteristic



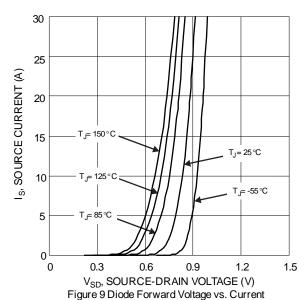
2 1.8 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) $V_{GS} = -10V$ 1.6 1.4 1.2 1 $V_{GS} = -4.5V$ 0.8 -3.5A 0.6 0.4 0.2 0 -50 0 25 50 75 100 125 150 T_J , JUNCTION TEMPERATURE (°C)

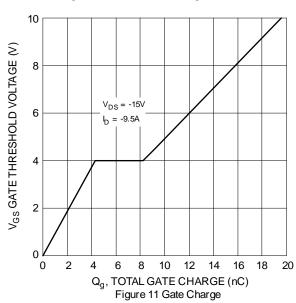
Figure 6 On-Resistance Variation with Temperature





 T_J , JUNCTION TEMPERATURE (°C) Figure 7 On-Resistance Variation with Temperature





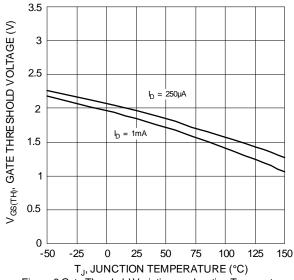
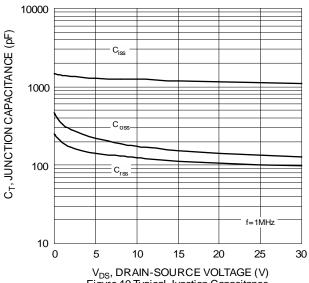
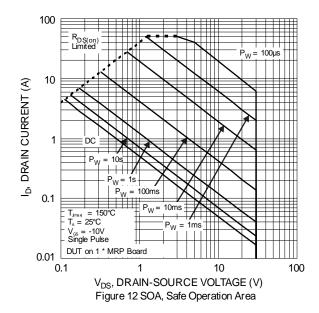


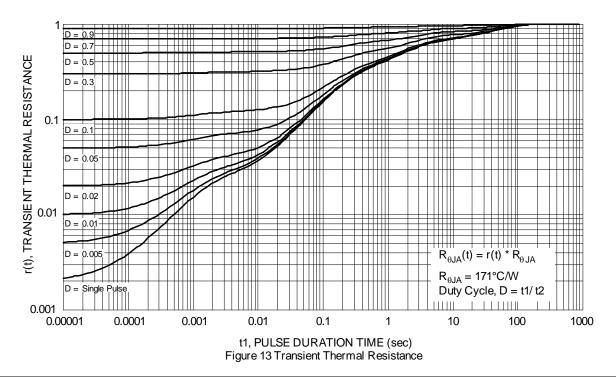
Figure 8 Gate Threshold Variation vs. Junction Temperature



 V_{DS} , DRAIN-SOURCE VOLTAGE (V) Figure 10 Typical Junction Capacitance

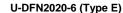


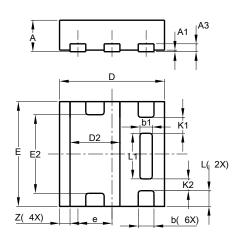




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.





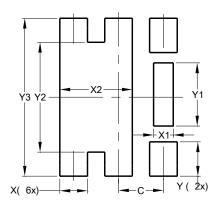
U-DFN2020-6							
Type E							
Dim	Min	Max	Тур				
Α	0.57	0.63	0.60				
A1	0	0 0.05 0.0					
A3	-	-	0.15				
b	0.25	0.35	0.30				
b1	0.185	0.285	0.235				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
E	1.95	2.05	2.00				
E2	1.40	1.60	1.50				
е	e – – 0.65						
L	0.25	0.35	0.30				
L1	0.82	0.92	0.87				
K1	_	_	0.305				
K2	_	_	0.225				
Z	-	_	0.20				
All Dimensions in mm							



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type E)



Dimensions	Value (in mm)			
С	0.650			
X	0.400			
X1	0.285			
X2	1.050			
Υ	0.500			
Y1	0.920			
Y2	1.600			
Y3	2.300			

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